

Development of a Diffusion Mobility Database for Cu-In-Se

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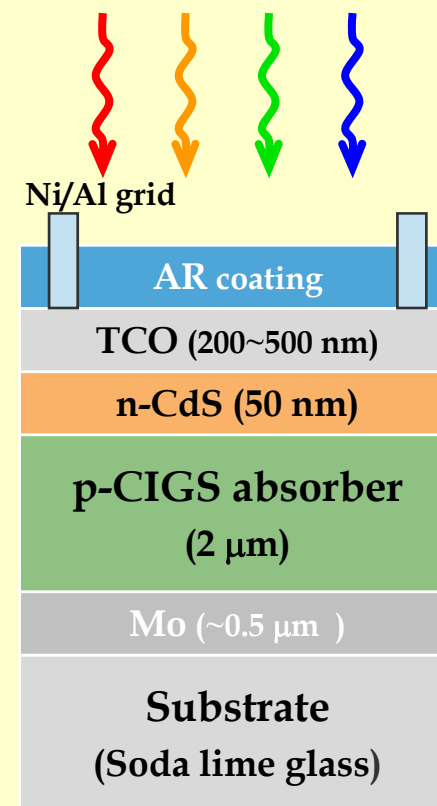
NIST

National Institute of Standards and Technology
Technology Administration, U.S. Department of Commerce

CIGS Solar Cell

Chalcopyrite $\alpha\text{-Cu(InGa)Se}_2$

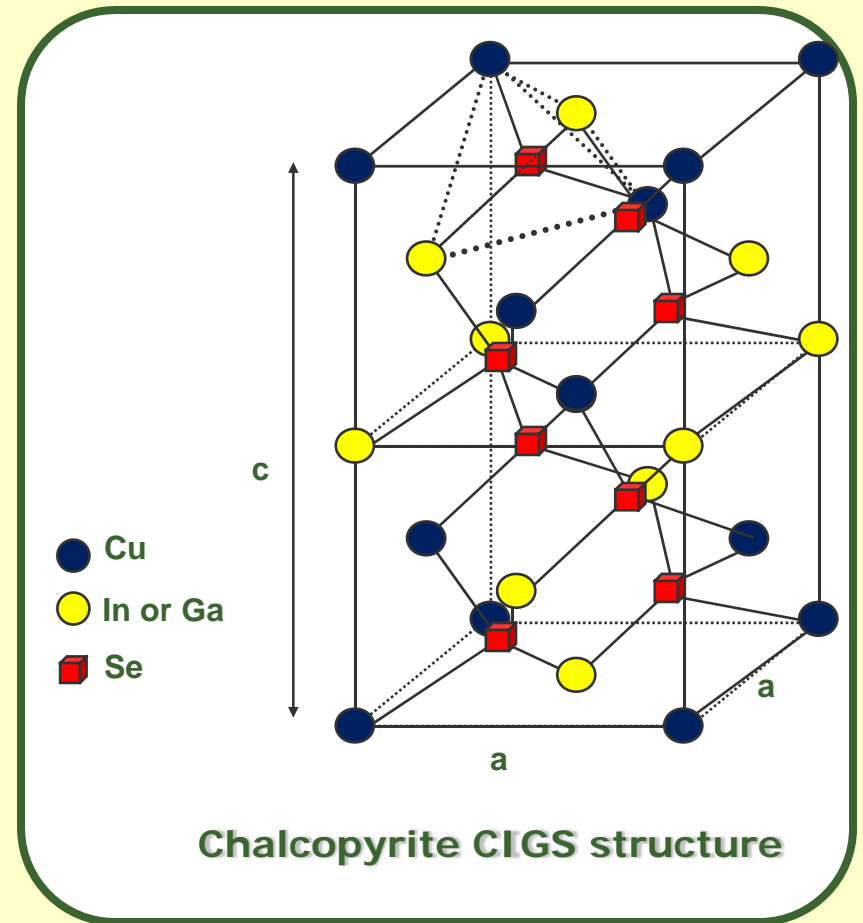
- A bilayer Ni/Al grid is used as a front contact material
- Anti-reflection (AR) coating (e.g., MgF₂)
- Transparent conducting oxide film: ZnO
- CdS buffer layer (n-type)
- **Polycrystalline CIGS layer**
 - acts as a p-type light absorber
 - forms a p-n junction with CdS
- Back contact electrode: Mo
- Substrate:
 - typically soda lime glass
 - flexible substrates: polymer and metal foils



Typical device structure

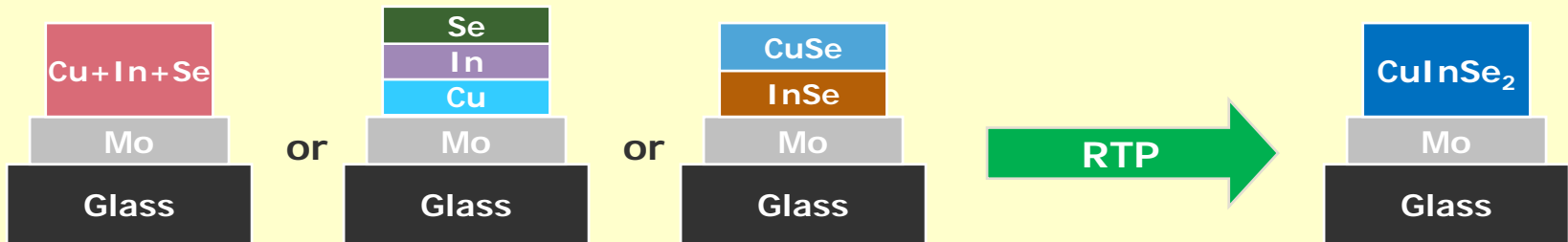
Chalcopyrite $\alpha\text{-Cu(InGa)Se}_2$

- Similar to Zinc-blende structure
- Cu and In are each surrounded by 4 anions (Se)
- Se is surrounded by 2 Cu and 2 In
- Se deficiency occurs as Cu occupies an interstitial position
- Lattice parameter ratio $c/a \approx 2$

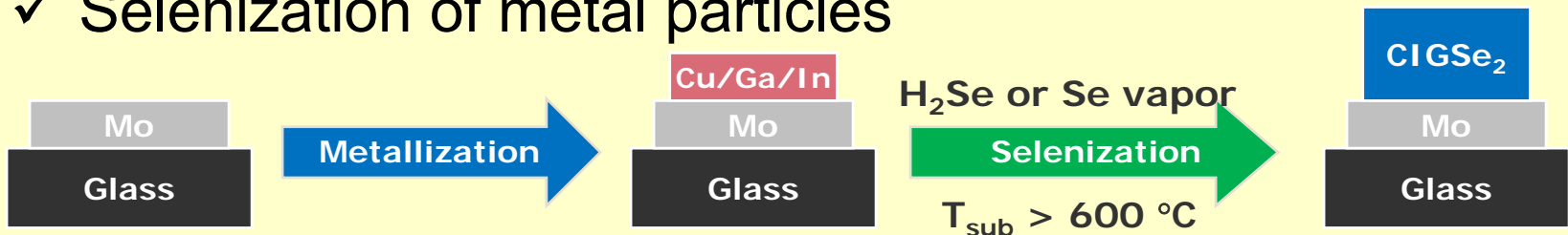


CIGS Processing Routes

- ✓ Co-Deposition of Elements (PVD, MBE etc)
 - High efficiency achieved with this method.
- ✓ Rapid thermal processing of stacked elemental layers

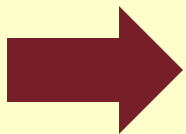


- ✓ Selenization of metal particles



GOAL

- **Need to make CIGS cost-effective need to reduce processing time from ~ 30 min to < 3 min.**
- **Need to develop methodology to predict processing pathways to achieve order magnitude decreases in processing time**



Develop diffusion mobility database for Cu-In-Ga-Se

CALPHAD Approach

Phase Equilibria & Thermodynamics

Experiments

DTA, Metallography,
X-ray Diffraction,
Calorimetry, EMF,
Vapor Pressure

Physics-based
Model Functions
with *Adjustable*
Parameters

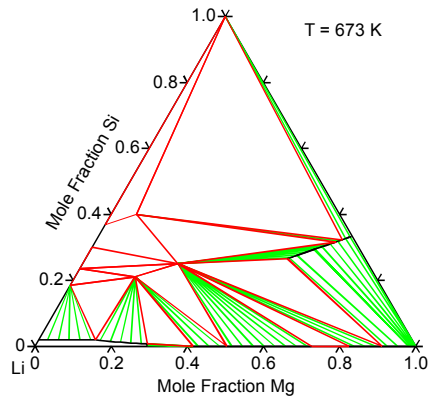
Theory

Quantum Mechanics,
Statistical Thermodynamics

Parameter
Optimization
for *Thermodynamic*
Description

Thermodynamic
Database

Applications
Solidification,
Phase Transformation Kinetics,
...



Diffusion

Experiments

Tracer, Intrinsic,
Chemical (Interdiffusion)

Theory

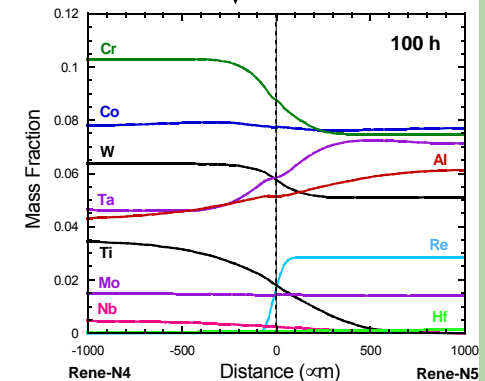
Atomistic
Calculations

Parameter
Optimization
for *Diffusion Mobility*
Description

Diffusion Mobility
Database

Thermodynamic
Factor

Thermodynamic
Factor



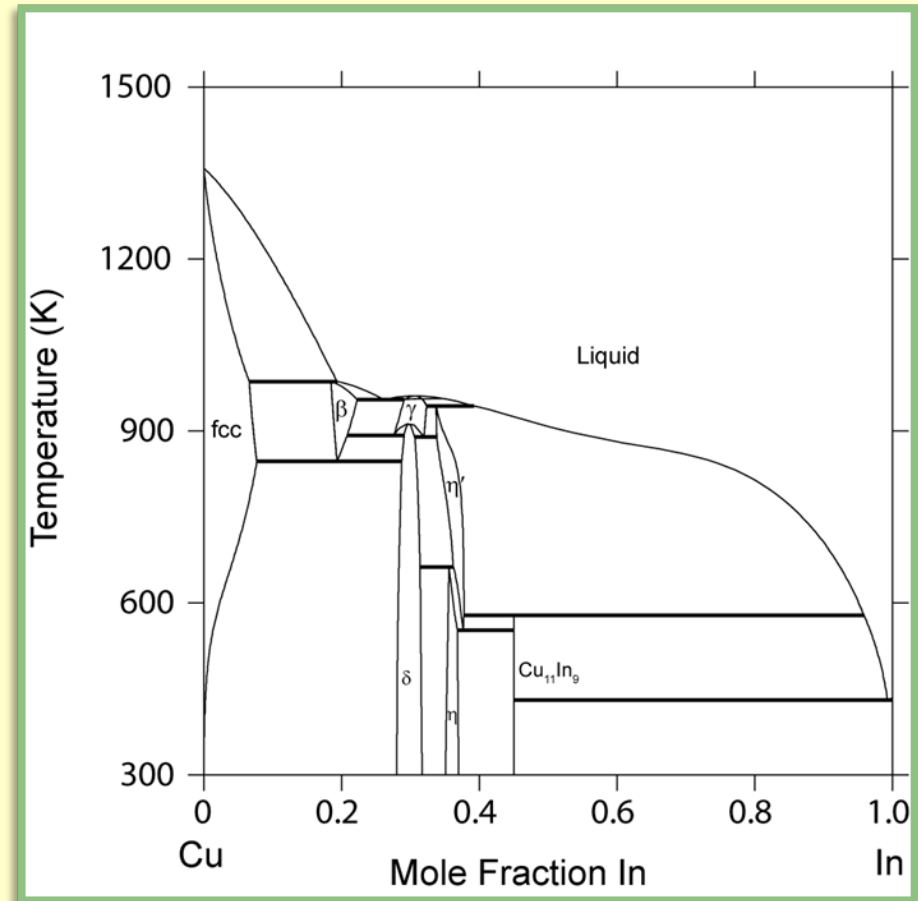
Published thermodynamic assessments

System	Reference
Cu-Ga	Li JB, Ji LN, Liang JK, Zhang Y, Luo J, Li CR, Rao GH. A thermodynamic assessment of the copper-gallium system. Calphad 2008;32:447.
Cu-In	Liu HS, Liu XJ, Cui Y, Wang CP, Ohnuma I, Kainuma ZP, Ishida K. Thermodynamic Assessment of the Cu-In Binary System. Journal of Phase Equilibria 2002;23:409.
Cu-In	Kao CR, Chen S-L, Chen SW, Chang YA. Phase Equilibria of the Cu-In System: II Thermodynamic Assessment and Calculation of Phase Diagram. Journal of Phase Equilibria 1993;14:22.
Cu-In	Hertz J, Aissaoui KE, Bouirden L. A Thermodynamic Optimization of the Cu-In System. Journal of Phase Equilibria 2002;23:473.
Cu-Se	Kim WK. STUDY OF REACTION PATHWAYS AND KINETICS IN $\text{Cu}(\text{In}_x\text{Ga}_{1-x})\text{Se}_2$ THIN FILM GROWTH. vol. PhD. Gainesville, FL: University of Florida, 2006.
Ga-Se	Zheng F, Shen JY, Liu YQ, Kim WK, Chu MY, Ider M, Bao XH, Anderson TJ. Thermodynamic optimization of Ga-Se system. Calphad 2008;32:432.
In-Se	Li J-B, Record M-C, Tedanac J-C. A thermodynamic assessment of the In-Se system. ZEITSCHRIFT FUR METALLKUNDE 2003;94:381.
Cu-In-Se	Shen J, Kim WK, Shang S, Chu M, Cao S, Anderson TJ. Thermodynamic description of the ternary compounds in the Cu-In-Se system. Rare metals 2006;25:481.

Cu-In Thermodynamics

- **3 solution phases:**
 - liquid, fcc(Cu) and β (bcc)
- **2 ordered phases:**
 - γ $(\text{Cu})_{0.654}(\text{Cu},\text{In})_{0.115}(\text{In})_{0.231}$
 - η $(\text{Cu})_{0.545}(\text{Cu},\text{In})_{0.122}(\text{In})_{0.333}$
- **3 stoichiometric phases:**
 - δ $(\text{Cu}_{0.7}\text{In}_{0.3})$,
 - η $(\text{Cu}_{0.64}\text{In}_{0.36})$
 - $\text{Cu}_{11}\text{In}_9$

Thermodynamics by Shen and Kim 2006



η phase modified for diffusion modeling and did not extended to ternary system



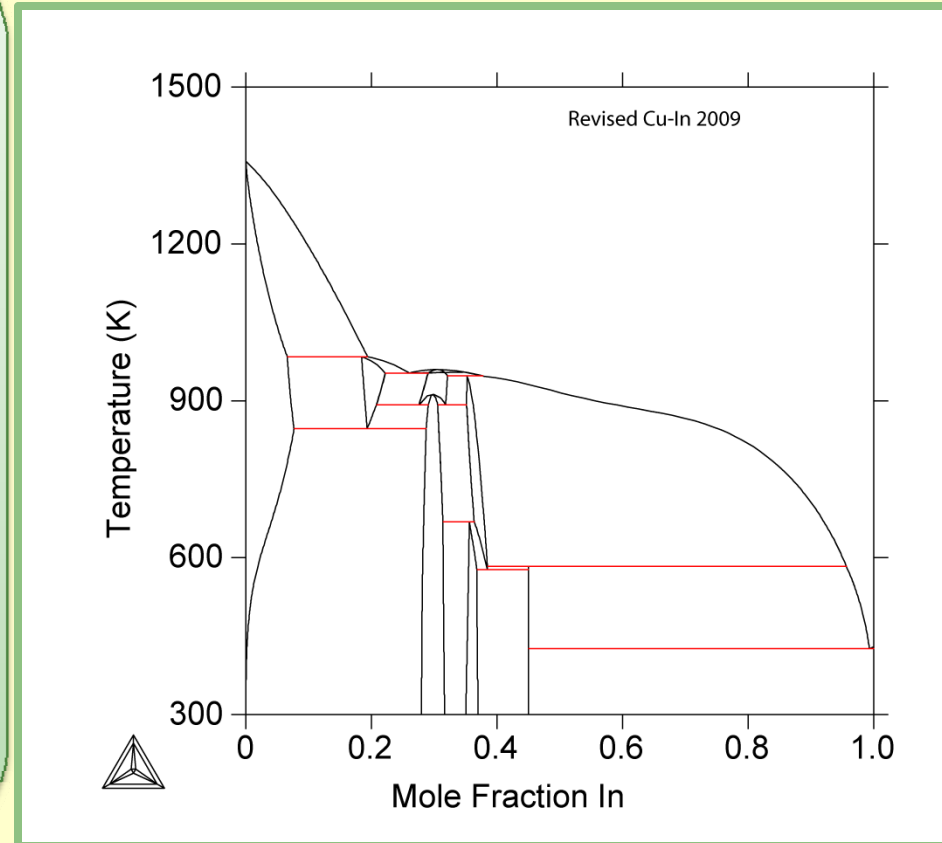
η (Cu,Va) (Cu) (In)

Cu-In Thermodynamics

Revised Description

- **3 solution phases:**
 - liquid, fcc(Cu) and β (bcc)
- **2 ordered phases:**
 - γ (Cu)_{0.654}(Cu,In)_{0.115}(In)_{0.231}
 - η (Cu)_{0.545}(Cu,In)_{0.122}(In)_{0.333}
- **3 stoichiometric phases:**
 - δ (Cu)_{0.7}In_{0.3},
 - η (Cu)_{0.64}In_{0.36}
 - Cu₁₁In₉

Thermodynamics by Shen and Kim 2006



η phase modified for diffusion modeling and did not
extended to ternary system



η (Cu,Va) (Cu) (In)

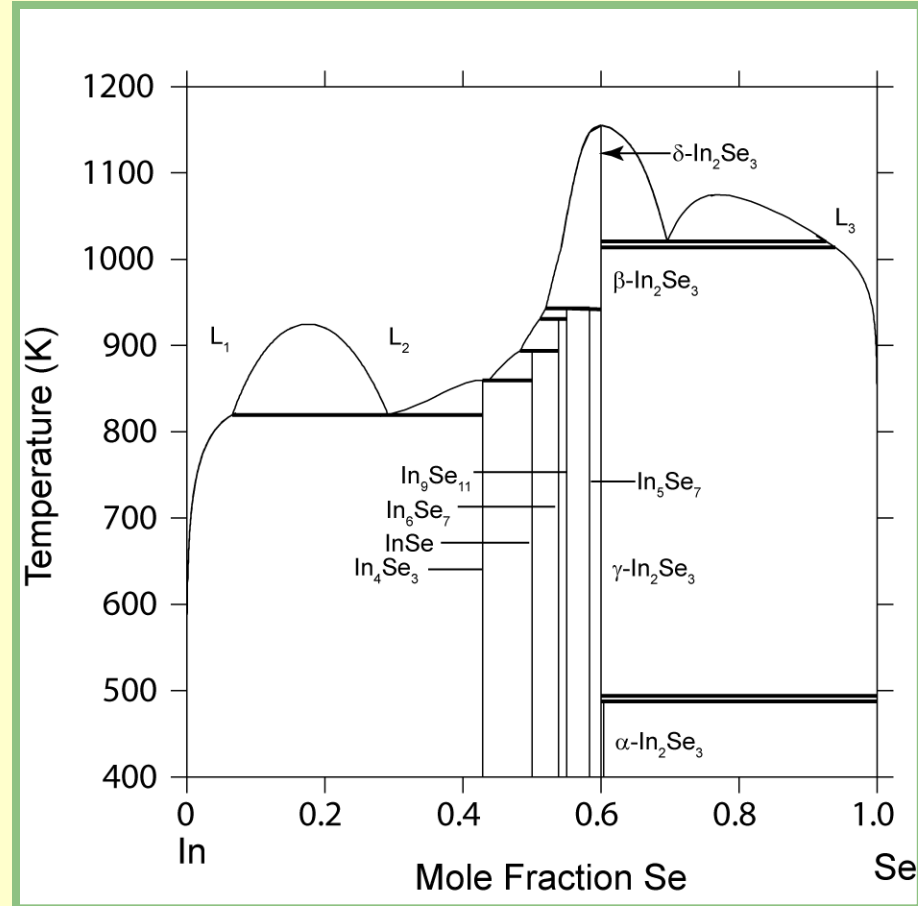
In-Se Thermodynamics

2 solution phases (Se and In)

➤ 1 ionic liquid

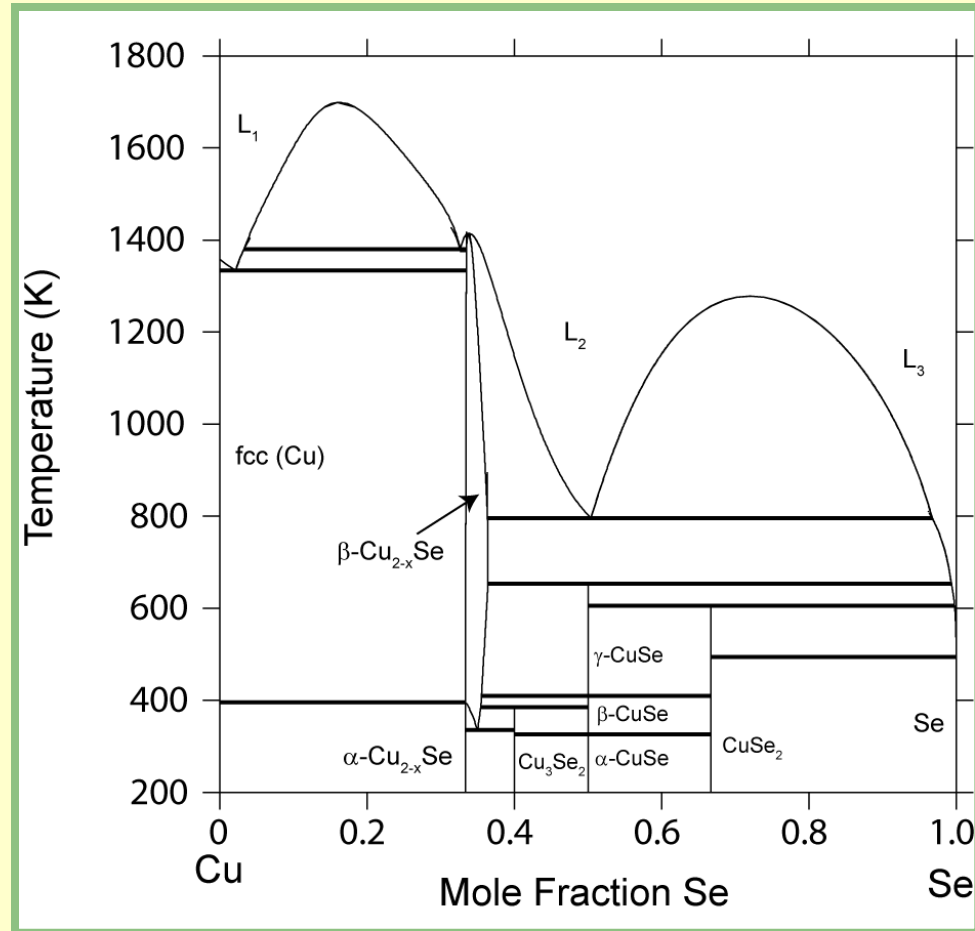
➤ 6 stoichiometric phases

- In_4Se_3 ,
- InSe ,
- In_6Se_7 ,
- $\text{In}_9\text{Se}_{11}$,
- In_5Se_7
- polymorphic In_2Se_3
(α , β , γ , and δ)



Cu-Se Thermodynamics

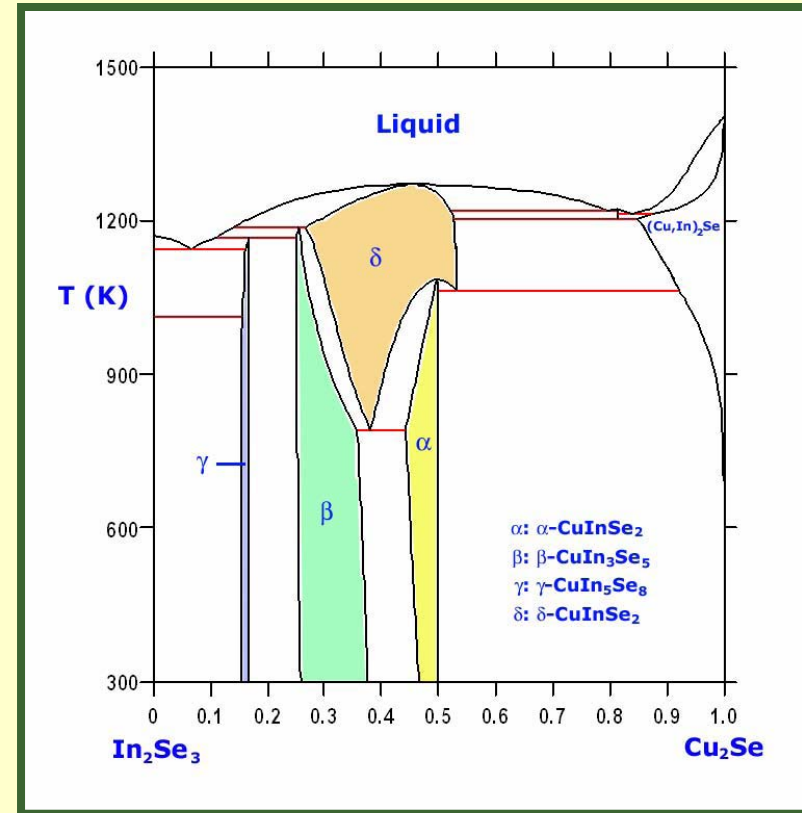
- **2 solution phases:**
 - fcc(Cu) and Se
- **1 ionic liquid**
- **1 ordered phases:**
 - Cu_2Se with 2 polymorphs (α and β)
- **3 stoichiometric phases:**
 - Cu_3Se_2
 - CuSe (α , β , γ)
 - CuSe_2



Cu-In-Se

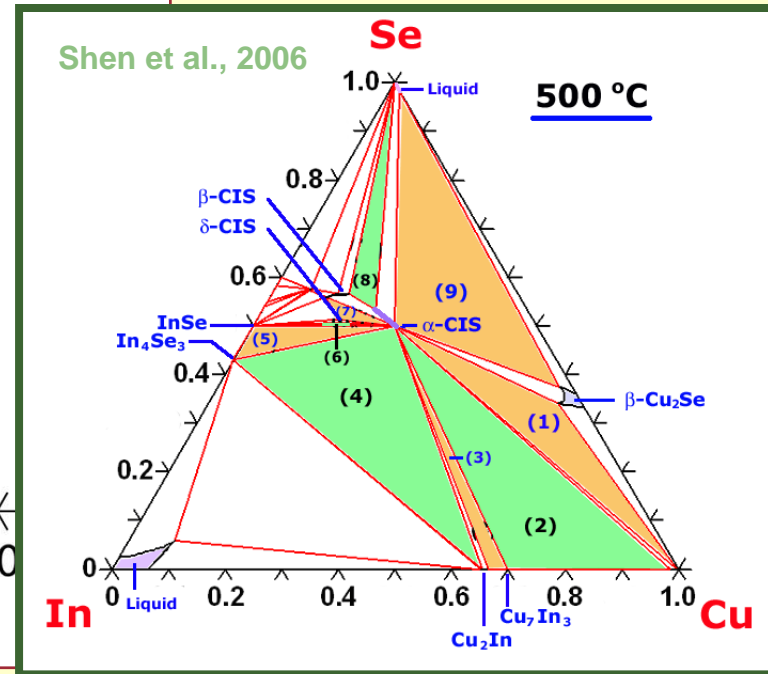
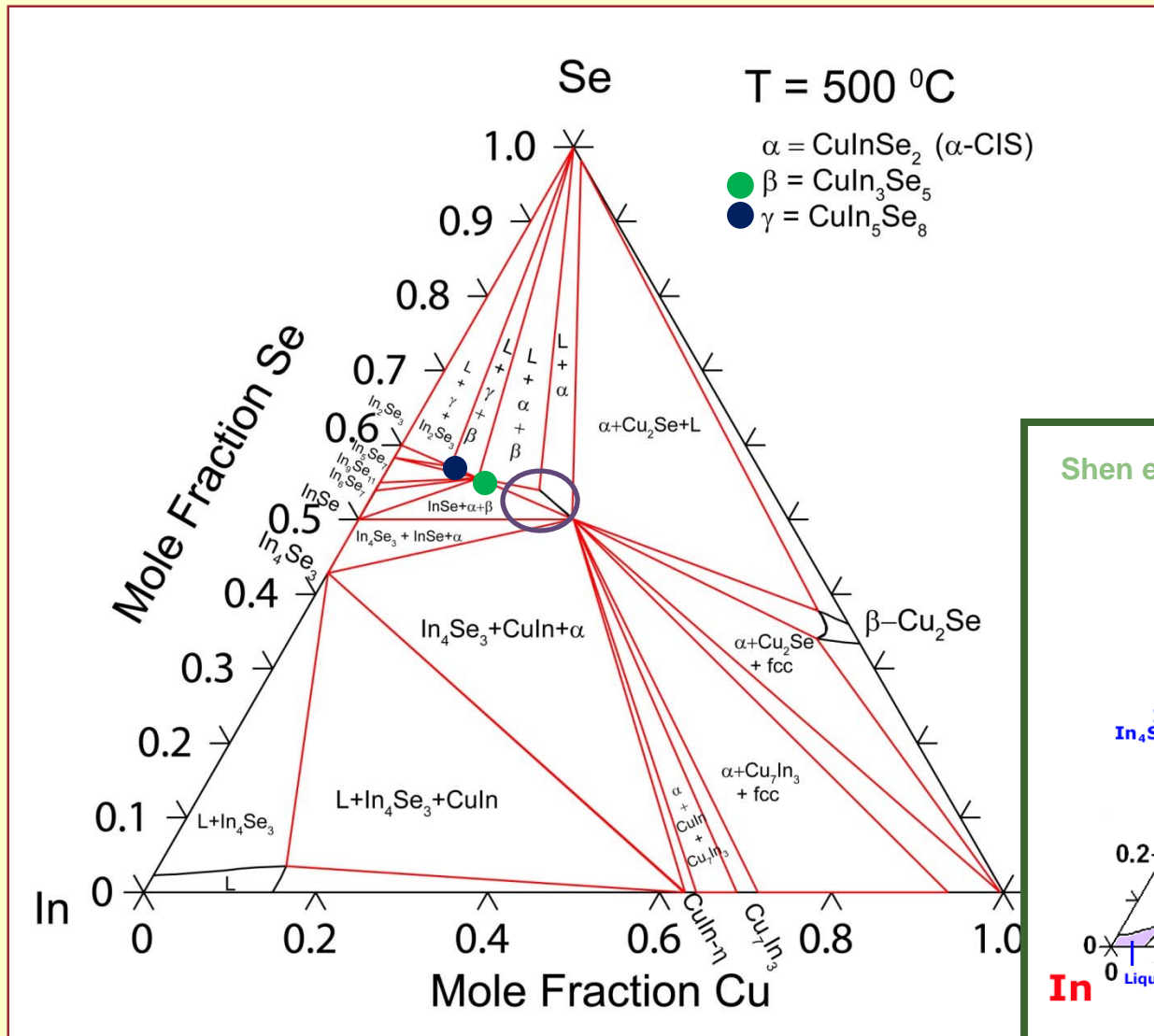
Ternary Phases

- 1 Ionic Liquid (Cu+1, In+3) (Se-2, Va, Se)
- α CuInSe₂ (Cu%,In,Va)(Cu,In%,Va)Se₂ (Chalcopyrite)
- δ CuInSe₂ (Cu%,In,Va)₂ Se (Se,Va)₂ (Sphalerite)
- β CuIn₃Se₅ (Cu%,In,Va) (Cu,In,Va)₃Se₅ (Defect Chalcopyrite)
- γ CuIn₅Se₈ (Cu%,In,Va) (Cu,In%,Va)₅ Se₈
- β Cu₂Se (Cu,Va) Se (Cu,In)



β and γ phases are treated as stoichiometric phases for the initial diffusion modeling

Cu-In-Se Thermodynamics



Diffusion Mobility Descriptions

➤ Inputs:

- Thermodynamics (CALPHAD approach)
- Diffusion experiments (unary, binary, ternary systems)
 - Tracer diffusivity,
 - Intrinsic diffusivity,
 - Interdiffusion coefficients/Marker motion

➤ Optimize value of mobilities, M_i , for all binaries consistent with available data

- Composition and Temperature-dependent
- Consistent with estimates of Metastable end members e.g., FCC W
- Optimized using code, DICTRA (Parrot)

$$M_i = \frac{M_i^0}{RT} \exp\left(\frac{-\Delta Q_i^*}{RT}\right) \text{ where } \Delta Q_i^* = f(c_i, T)$$

$$M_i^0 \text{ is exponentially dependent on composition } M_i = \frac{1}{RT} \exp\left(\frac{\Delta Q_i^*}{RT}\right)$$

$$\Delta Q_i = \Delta Q_i^* - RT\Theta_i \quad \text{and} \quad M_i^0 = \exp(\Theta_i)$$

$$\Delta Q_i = \sum_{p=1}^n x_p Q_i^p + \sum_p \sum_{q>p}^n x_p x_q \left[\sum_{r=0}^m {}^r A_i^{pq} (x_p - x_q)^r \right] + \sum_p \sum_{q>p} \sum_{v>q} x_p x_q x_v \left[v_{pqv}^s {}^s B_i^{pqv} \right]$$

Assessment of Diffusion Mobilities

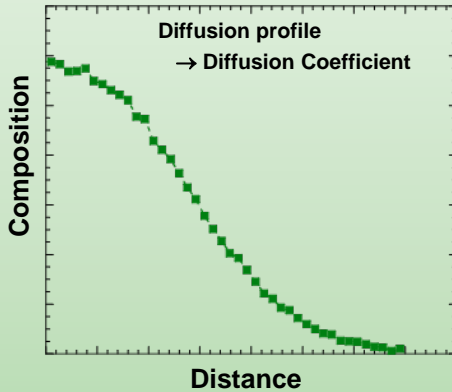
Estimate Mobility

Compare experimental and calculated D

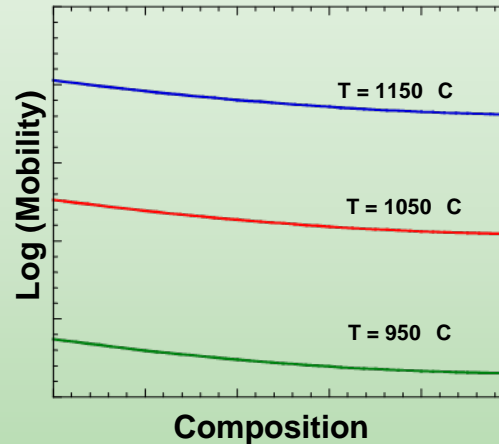
Simulate diffusion process

Adjust Mobility

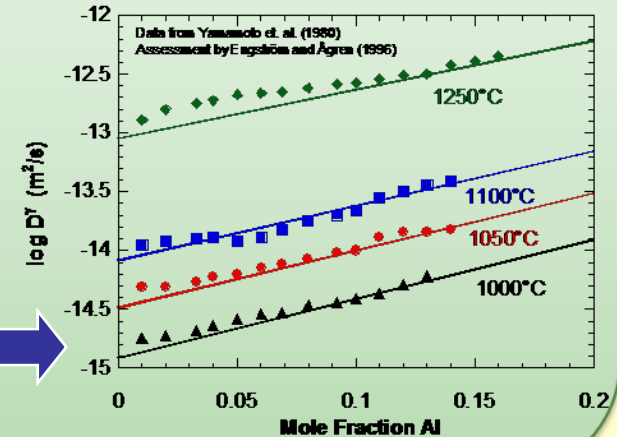
Experimental diffusion data



Mobility $M=f(c,T)$



Calculate diffusion Coefficients $D = f(c,T)$
Ni - Al



$$M_i = \frac{M_i^\circ}{RT} \exp\left(\frac{-\Delta Q_i}{RT}\right) \text{ where } \Delta Q_i = f(c_i, T)$$

$$\text{For a binary: } Q_i^\phi = c_i Q_i^i + c_j Q_j^j + c_i c_j (A_i^{i,j} + (c_i - c_j) B_i^{i,j} + (c_i - c_j)^2 C_i^{i,j} + \dots)$$

Diffusion Modeling Challenges

- Stoichiometric compounds
- Ternary intermetallic phases
- Anisotropic crystal structures
- Lots of missing data
- Many reactions are promoted by epitaxy: vacancy-driven diffusion is not the dominate diffusion mechanism.

- $D_{\text{eff}} = D_{\text{bulk}} + D_{\text{stress}} + D_{\text{gb}} + D_{\text{ele}}$

Disordered Phases: FCC

$$M_i = \frac{M_i^\circ}{RT} \exp\left(\frac{-\Delta Q_i^*}{RT}\right) \text{ where } \Delta Q_i^* = f(c_i, T)$$

- **Cu self diffusion and fcc-In self diffusion taken from previous assessment work.**
- **Cu-In parameter evaluated based on experimental work.**
- **Self diffusion for fcc Se based on diffusion correlations of Brown and Ashby (after calculating a metastable fcc melting temperature for Se)**

$$\Delta^{fcc} Q_{Cu}^* = x_{Cu} Q_{Cu}^{Cu} + x_{In} Q_{Cu}^{In} + x_{Se} Q_{Cu}^{Se} + x_{Cu} x_{In} Q_{Cu}^{Cu,In}$$

$$\Delta^{fcc} Q_{In}^* = x_{Cu} Q_{In}^{Cu} + x_{In} Q_{In}^{In} + x_{Se} Q_{In}^{Se} + x_{Cu} x_{In} Q_{In}^{Cu,In}$$

$$\Delta^{fcc} Q_{Se}^* = x_{Cu} Q_{Se}^{Cu} + x_{In} Q_{Se}^{In} + x_{Se} Q_{Se}^{Se}$$

Both Se and In have anisotropic crystal structures.

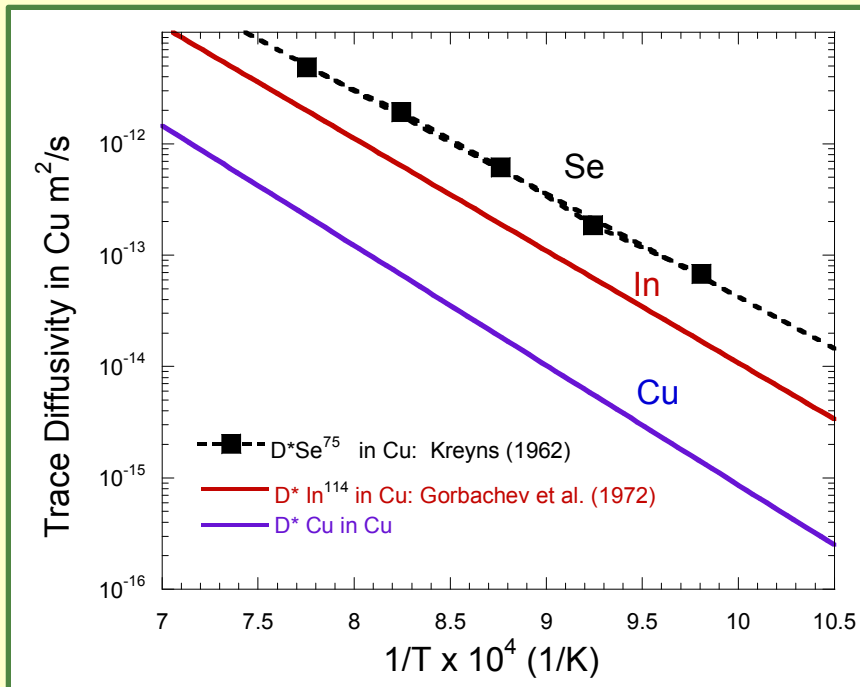
- **Use average values or value for the fastest diffusion directions.**

Disordered Parameters

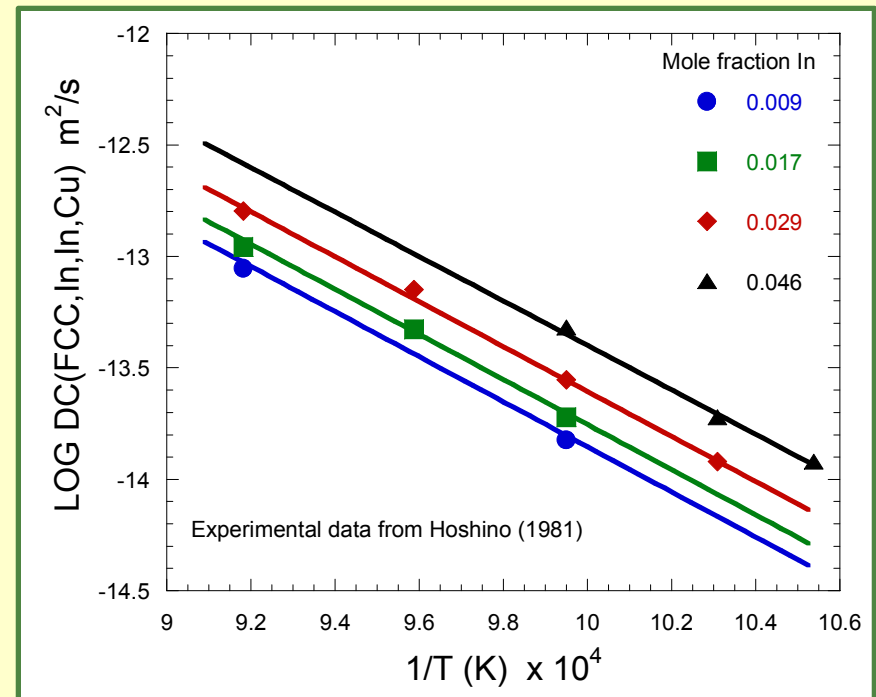
Parameter	Value	Reference
${}^{fcc}Q_{Cu}^{Cu}$	$-205872+R*T*LN(4.889e-5)$	[Ghosh, 2001]
${}^{fcc}Q_{Cu}^{In}$	$-120904+R*T*LN(8.3e-5)$	This work
${}^{fcc}Q_{Cu}^{Se}$	$-120904+R*T*LN(8.3e-5)$	This work (treat like In)
${}^{fcc}Q_{Cu}^{Cu,In}$	$+691337-346*T$	This work
${}^{fcc}Q_{In}^{Cu}$	$-193000+R*T*LN(1.3e-4)$	This work (based on [Hoshino K, 1981,1982])
${}^{fcc}Q_{In}^{In}$	$-111000+R*T*LN(4.47e-4)$	[Ghosh, 1998]
${}^{fcc}Q_{In}^{Se}$	$-193000+R*T*LN(1.3e-4)$	This work (treat like Cu in fcc-In)
${}^{fcc}Q_{In}^{Cu,In}$	$+100405$	This work
${}^{fcc}Q_{Se}^{Cu}$	$-177187+R*T*(7.6e-5)$	This work (based on [Kreyns, 1962])
${}^{fcc}Q_{Se}^{In}$	$-177187+R*T*(7.6e-5)$	This work Treat like Se in fcc-Cu
${}^{fcc}Q_{Se}^{Se}$	$-47566 +R*T*LN(1.0e-5)$	This work (Brown Ashby correlation)
${}^{In-bct}Q_{In}^{In}$	$-78240+R*T*LN(3.2e-4)$	This work (based on [Dickey, 1959])
${}^{tri}Q_{Se}^{Se}$	$-115822+R*T*LN(8.2e-7)$	This work (based on [Günther, 1985])
${}^{tri}Q_{In}^{Se}$	$-7400+R*T*LN(5.6e-10)$	[Akhundov, 1958]

Diffusion in FCC

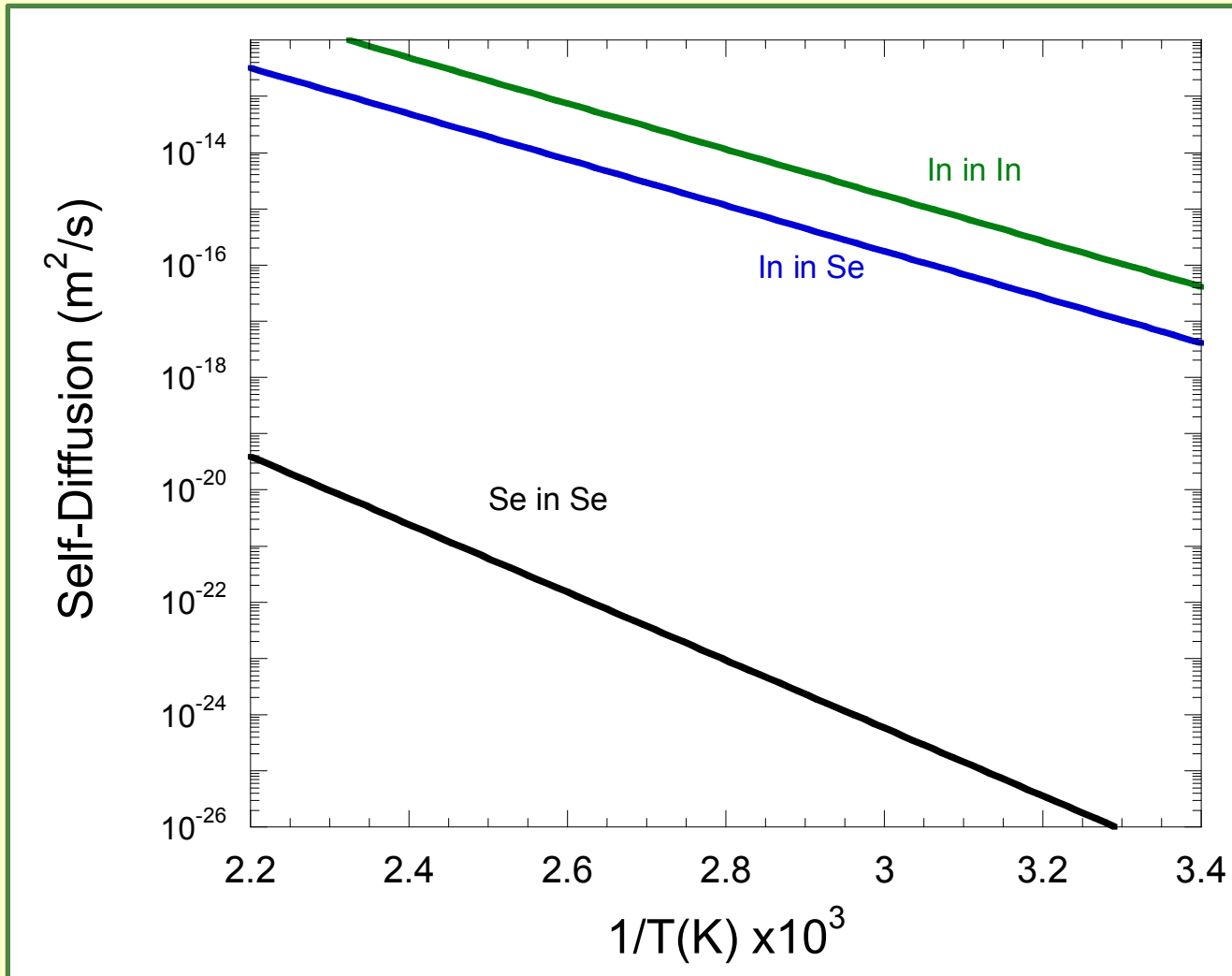
Tracer Diffusivity



Interdiffusion



In and Se tracer diffusivity



Modeling of Stoichiometric Intermetallic Phases

- Generally only a single interdiffusion coefficient available.
- Model with no composition dependence; all the parameters are set equal.
- Using “GENERAL” diffusion model in DICTRA
 - Mobilities on the individual sublattices are summed.
 - Example: (A,B)(A,B)₂

- $$M(\text{PHASE}, A\#1) = \left(y'_A y''_B M'_{A:B} + y'_B y''_A M'_{B:A} \right) \frac{y'_A}{RT}$$

- $M(\text{Phase}, A) = M(\text{PHASE}, A\#1) + M(\text{PHASE}, A\#2)$

$$D_A^* = \left(y'_A M'_A + y''_A M''_A \right) \frac{RT}{u(A)}$$

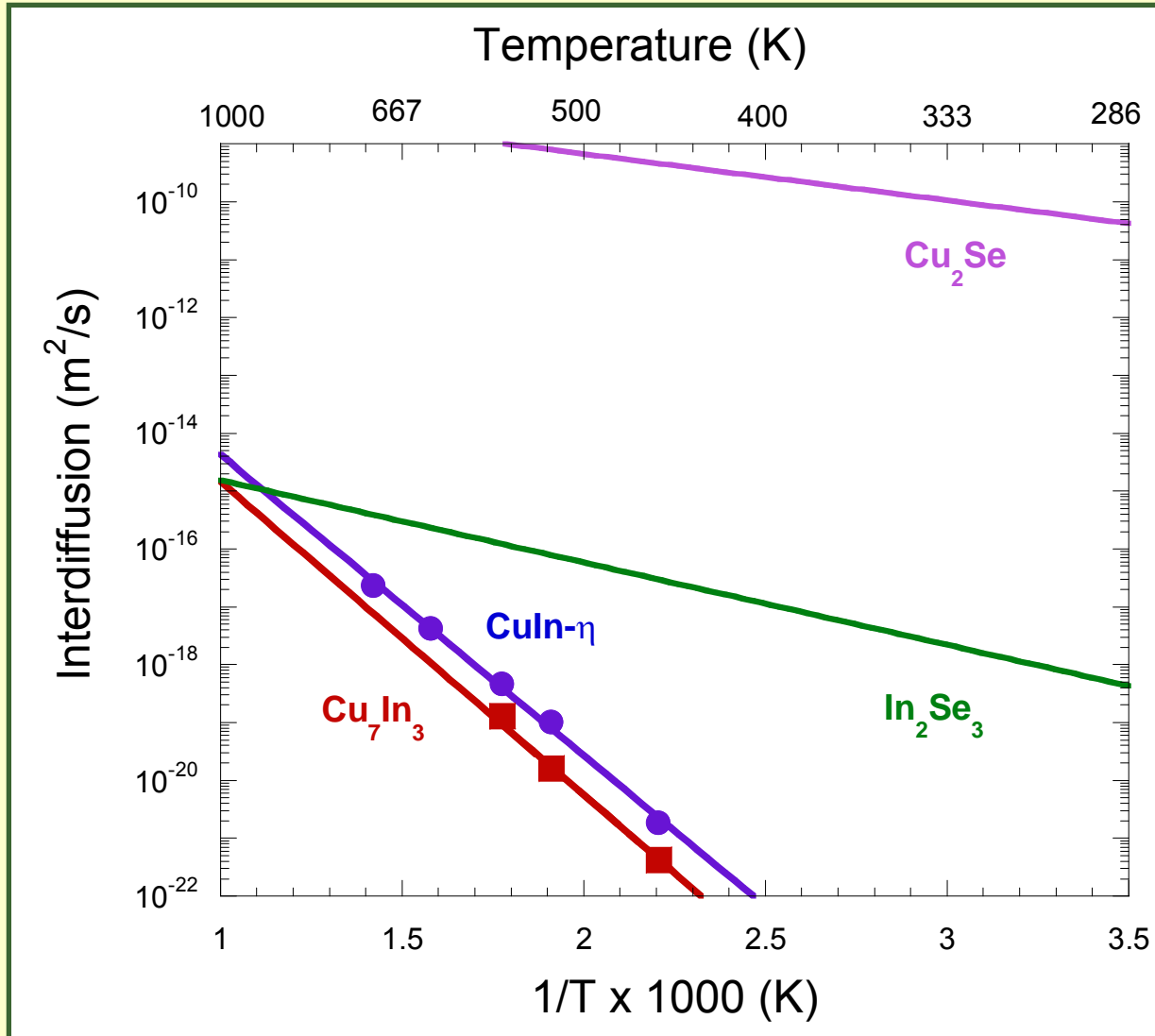
- where $u(A)$ = total number of atoms of A.

Applied to Cu-In: δ (Cu_{0.7}In_{0.3}), η (CuIn) and Cu₁₁In₉

In-Se: In₄Se₃, InSe, In₆Se₇, In₉Se₁₁, In₅Se₇ and the polymorphic In₂Se₃

Cu-Se: Cu₃Se₂ CuSe (α , β , γ) Cu₂Se

Comparison of Interdiffusion in Various Intermetallics in Cu-In-Se



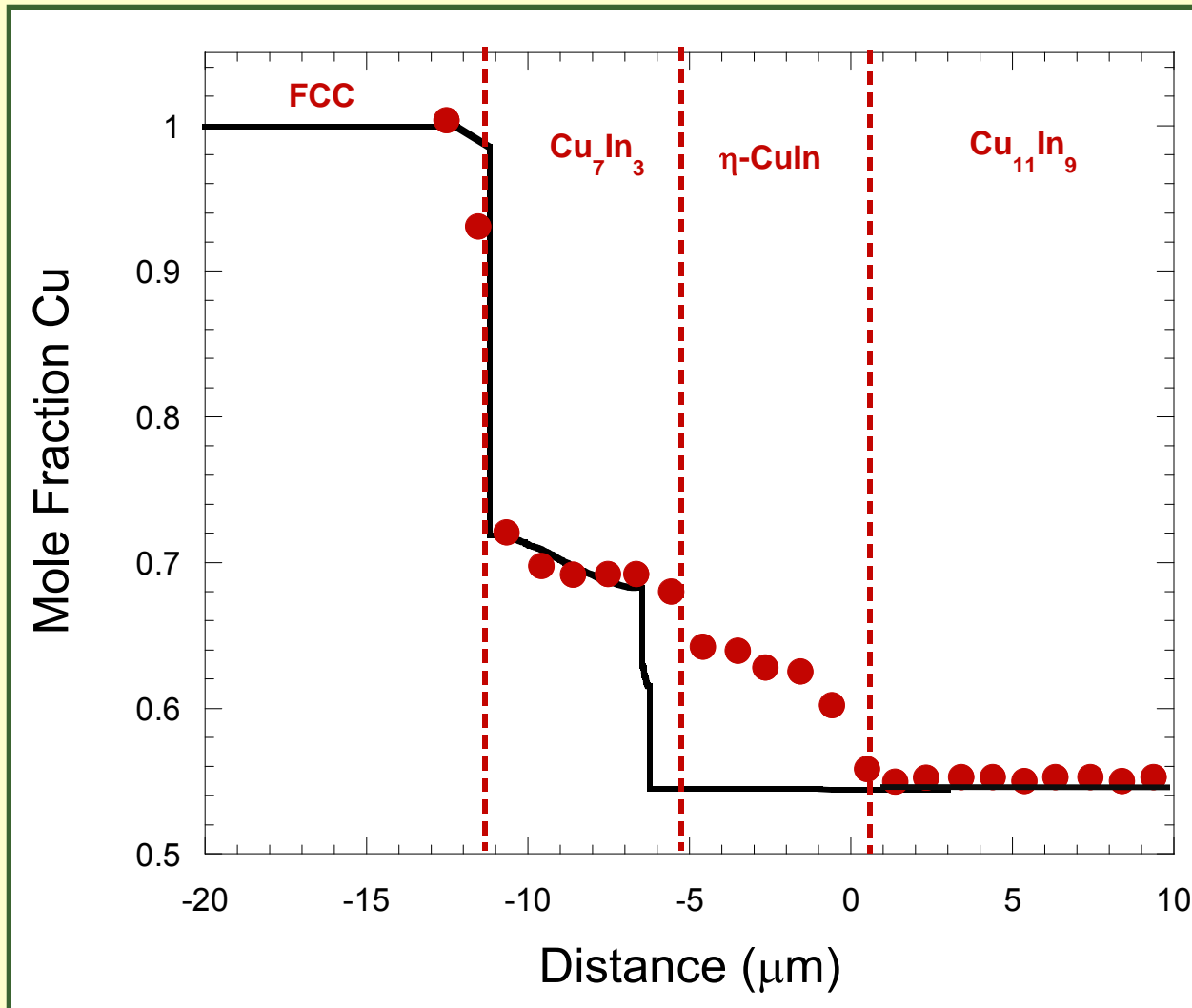
$$MQ(Cu_7In_3) = -105000 + R \cdot T \cdot \ln(1.0e-9)$$

$$MQ(CuIn-\eta) = -108700 + R \cdot T \cdot \ln(2.0e-10)$$

$$MQ(In_2Se_3) = -27245 + R \cdot T \cdot \ln(4.1e-14)$$

$$MQ(Cu_2Se) = -15359 + R \cdot T \cdot \ln(2.7e-08)$$

Cu/In/Cu Solder Joints at 290 °C for 16 days



● Sommadossi, et al. 2003

Time = 0 s



Note : Diffusion in Cu₁₁In₉ must be adjusted.

Diffusion Model for Ternary Intermetallics

α -CuInSe₂: (Cu%,In,Va)(Cu,In%,Va)Se₂

- Diffusion via Cu vacancies dominates. (Dagen 1992)

$$D_{Cu}^* = \frac{RT}{u_{Cu}} (y'_{Cu} M'_{Cu} + y''_{Cu} M''_{Cu})$$

$$D_{In}^* = \frac{RT}{u_{Cu}} (y'_{In} M'_{In} + y''_{In} M''_{In})$$

$$D_{Se}^* = \frac{RT}{u_{Se}} (M'''_{Se})$$

Similar approach applied to:

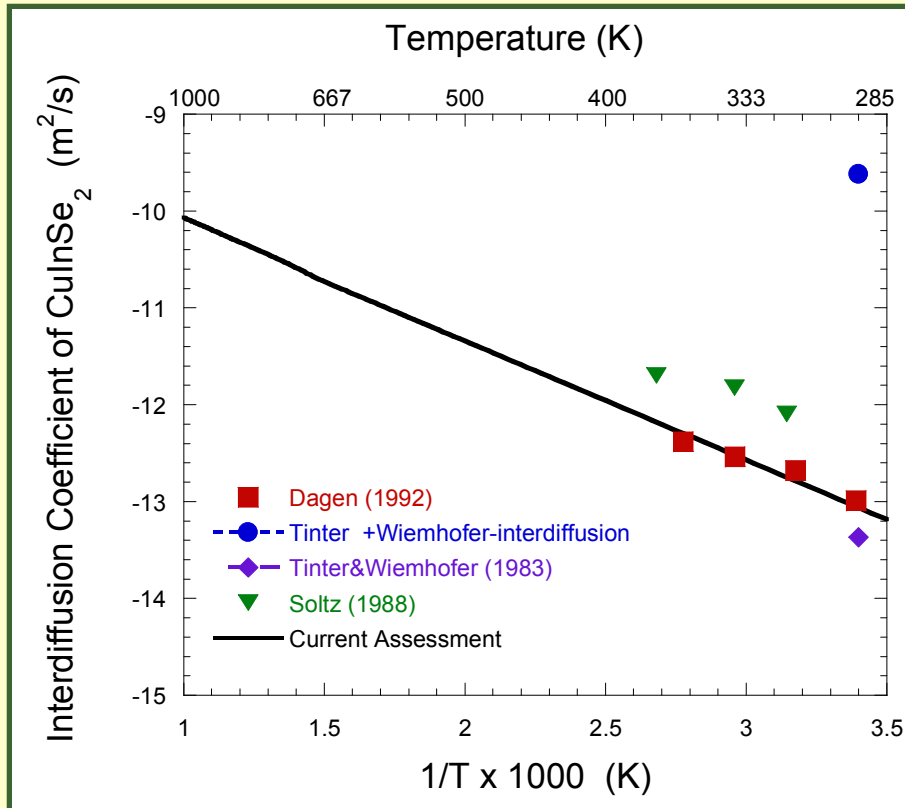
δ CuInSe₂ (Cu%,In,Va)₂ Se (Se,Va)₂

β CuIn₃Se₅ (Cu%,In,Va)(Cu,In,Va)₃Se₅

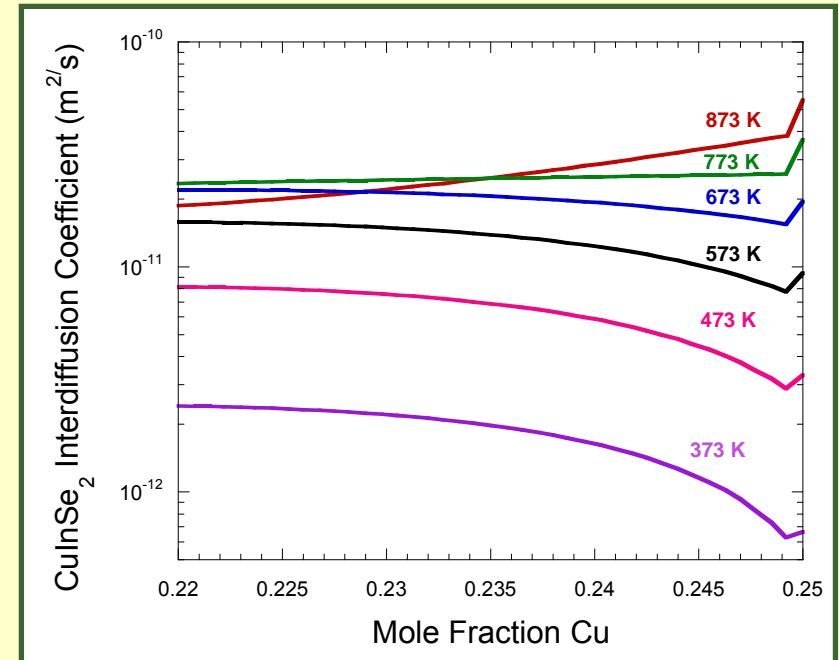
γ CuIn₅Se₈ (Cu%,In,Va) (Cu,In%,Va)₅ Se₈

Interdiffusion Coefficients in $\alpha\text{-CuInSe}_2$

Measured and Calculated
Temperature Dependence



Predicted Composition Dependence



$\alpha\text{-CuInSe}_2$ diffusion mobilities modeled using general model

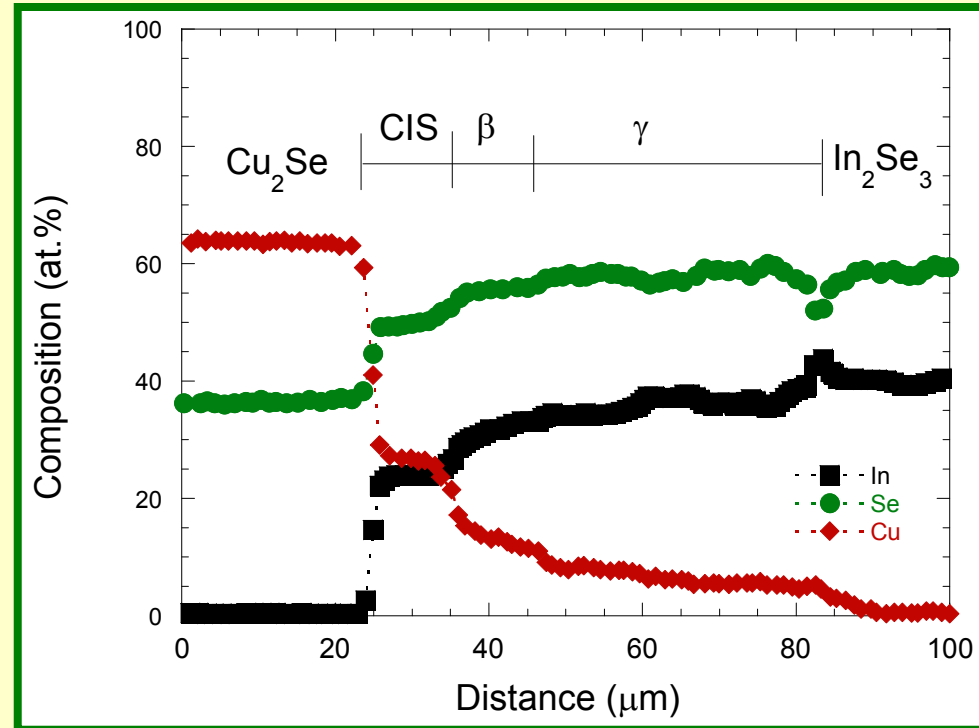
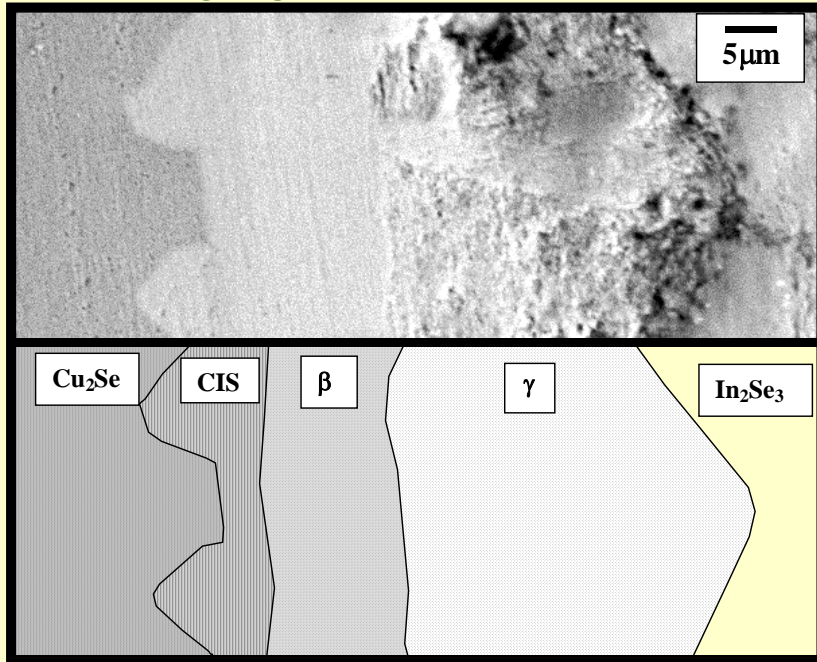
$$Q = -25050 \text{ J/mole}; M_0 = 9.975\text{e-}10 \text{ m}^2/\text{s}$$

$\text{Cu}_2\text{Se}/\text{In}_2\text{Se}_3$ Diffusion Couple at 550 °C for 1.5 h

CIS = CuInSe_2

β = defect chacopyrite (CuIn_3Se_5)

γ = CuIn_5Se_8

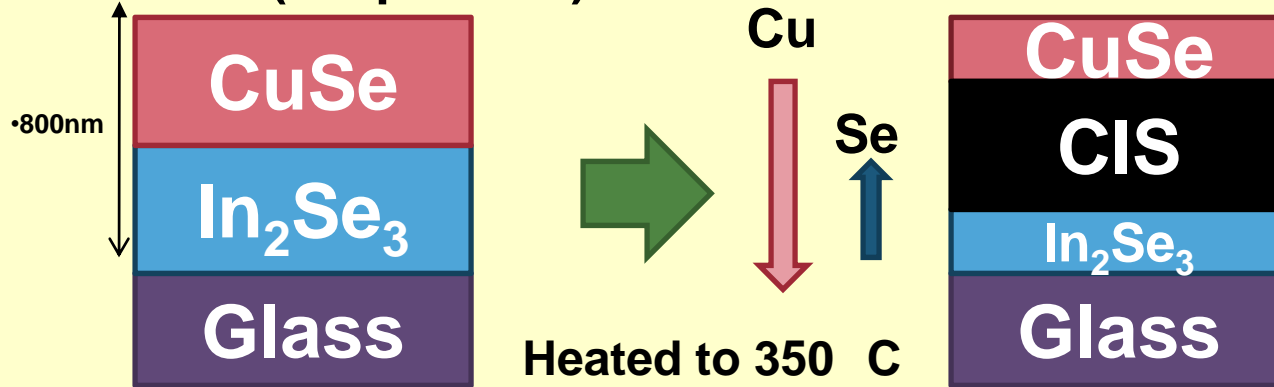


- Estimate of In diffusion in Cu_2Se = 4.2×10^{-10} m²/s
- Defect structure leads to rapid diffusion.
- In diffuses via an ionic lattice diffusion through the Cu vacancy sites on Cu_2Se

Type of Reactions to Simulate

Kim et. al., *J. Phys. Chem. Solids*, 2005. : CuSe/In₂Se₃ precursor

CIS + Se (evaporated)



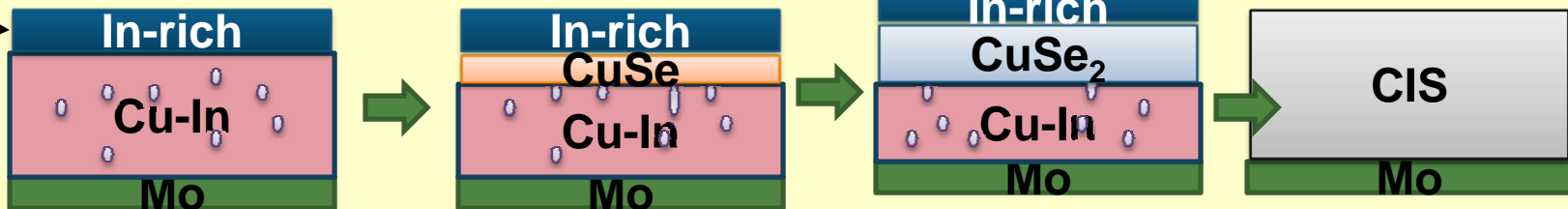
Activation energy 162 +/- 5 KJ/mol (parabolic model)

J. Crystal Growth , 2005. : Cu/In selenization

$\text{CuSe} + \text{In} + n\text{Se (vapor)} \rightarrow \text{CuSe}_2 + \text{In} + n\text{Se (vapor)} \rightarrow \text{CIS}$

Se vapor

Possible liquid In??



Activation energy 124 +/- 19 kJ/mol (Avrami model); 100 +/- 14 kJ/mol parabolic

Conclusions



Significant challenges

- ✓ **Lack of data**
 - Use diffusion correlations
 - Extract activation energies
 - Estimate from bulk diffusion couples
- ✓ **Anisotropic crystal structures**
 - Treat average diffusion (assume polycrystalline)
- ✓ **Diffusion models**
 - Models have developed and are in the process of being implemented
- ✓ **Enhanced diffusion due to coherency relations**
 - Mechanisms available to adjust thermodynamics and diffusion activation energies

These challenges can be overcome